

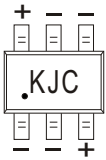
Plastic-Encapsulate Diodes

SWITCHING DIODE

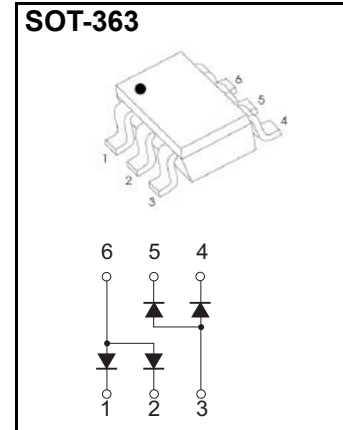
FEATURES

- Fast Switching Speed
- Ultra-Small Surface Mount Package
- For General Purpose Switching Applications
- High Conductance

MAKING: KJC



Solid dot = Pin1 indicate.
Solid dot = Green molding compound device,
if none, the normal device.



Maximum Ratings @Ta=25°C

Parameter	Symbol	Limit	Unit
Peak Repetitive Peak Reverse Voltage	V_{RRM}	75	V
Working Peak Reverse Voltage	V_{RWM}		
DC Blocking Voltage	V_R		
Forward Continuous Current	I_{FM}	300	mA
Average Rectified Output Current	I_O	150	mA
Non-Repetitive Peak Forward Surge Current @ t=8.3ms	I_{FSM}	2	A
Power Dissipation	P_D	200	mW
Thermal Resistance From Junction to Ambient	$R_{\theta JA}$	625	°C/W
Operating Junction Temperature	T_J	150	°C
Storage Temperature	T_{STG}	-55~+150	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Reverse breakdown voltage	$V_{(BR)}$	$I_R = 2.5\mu A$	75		V
Reverse voltage leakage current	I_R	$V_R = 75V$ $V_R = 20V$		2.5 0.025	μA
Forward voltage	V_F	$I_F = 1mA$ $I_F = 10mA$ $I_F = 50mA$ $I_F = 150mA$		715 855 1000 1250	mV
Capacitance between terminals	C_T	$V_R = 0, f = 1MHz$		2	pF
Revers recovery time	t_{rr}	$I_F = I_R = 10mA, I_{rr} = 0.1 \times I_R,$ $R_L = 100\Omega$		4	ns



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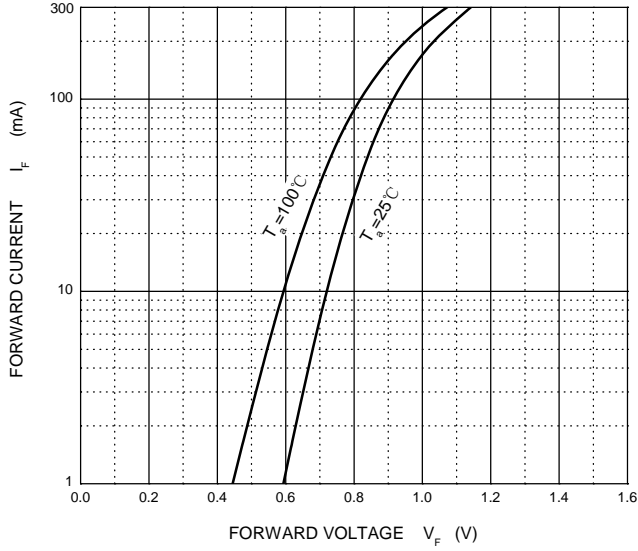
SOT-363

BAW56DW

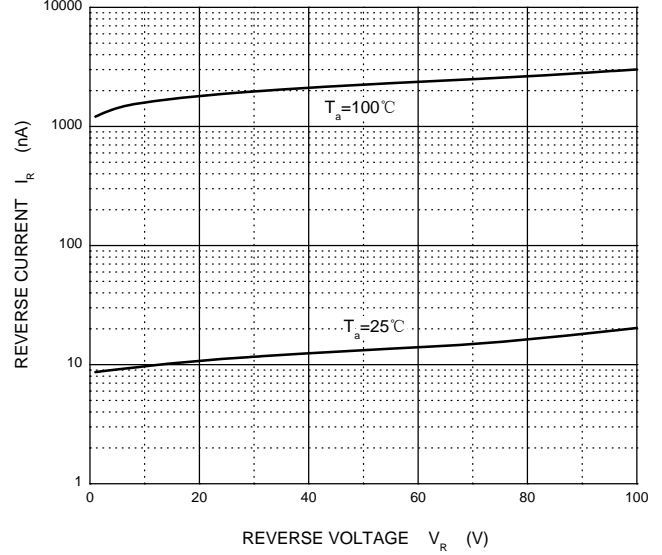


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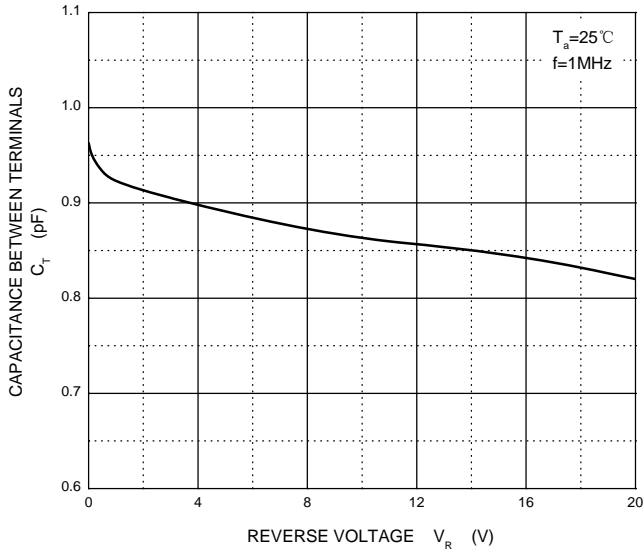
Forward Characteristics



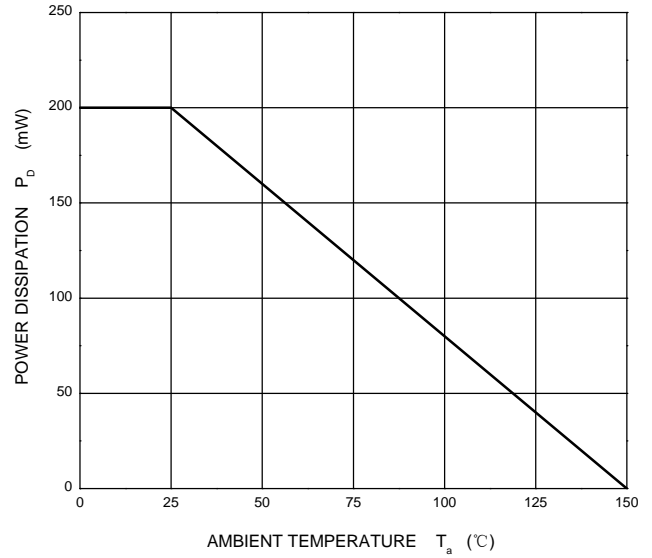
Reverse Characteristics



Capacitance Characteristics

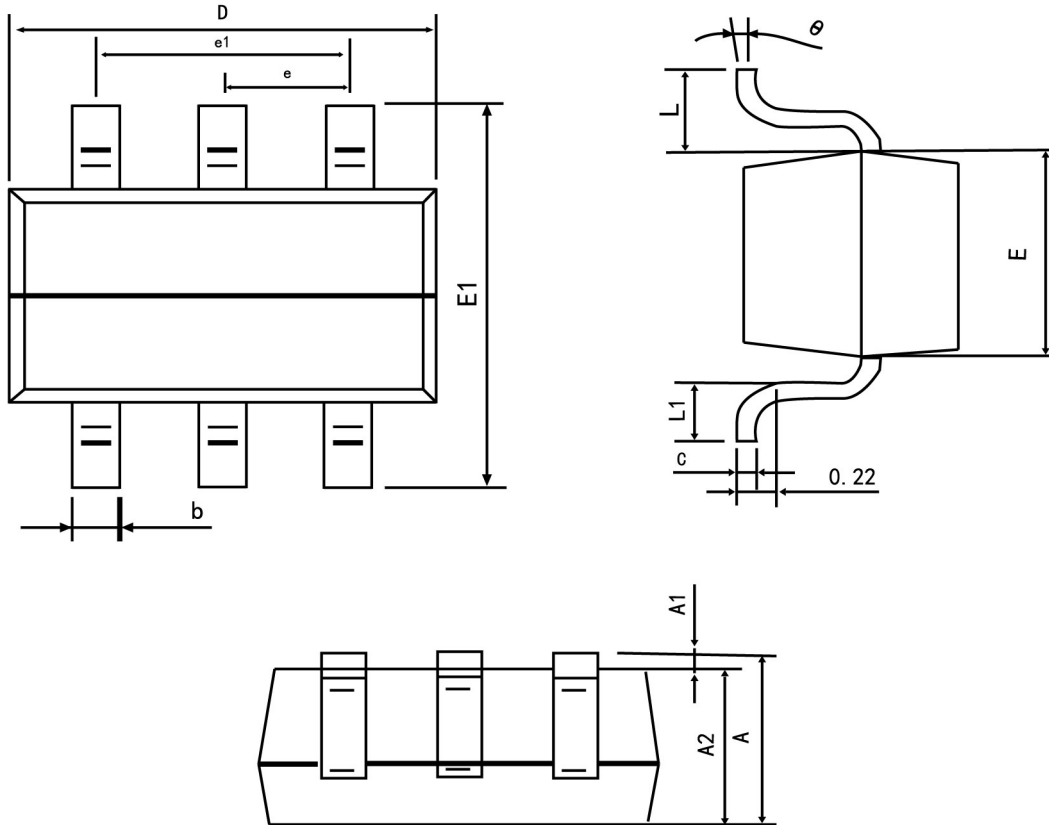


Power Derating Curve





SOT-363-Package Outline Dimensions



Symbol	Dimension in Millimeters	
	Min	Max
A	0.900	1.100
A1	0.000	0.100
A2	0.900	1.000
b	0.150	0.350
c	0.080	0.150
D	2.000	2.200
E	1.150	1.350
E1	2.150	2.450
e	0.650 TYP	
e1	1.200	1.400
L	0.525 REF	
L1	0.260	0.460
θ	0°	8°